NSN 5962-01-314-9189

Memory Microcircuit - Page 1 of 1



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Maximum Power Dissipation Rating:

495.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Electrostatic sensitive and hermetically sealed and burn in and monolithic

Inclosure Material:

Ceramic

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

16 input

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

7.0 volts power source

Time Rating Per Chacteristic:

75.00 nanoseconds propagation delay time, low to high level output and 75.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Ram

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

28 leadless

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

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